

Computational design of novel 2D electronic and magnetic materials

Abstract

Theoretical design based on first-principles computations play an important role in the research and innovation of 2D materials. In the past few years, our group has designed a series of novel 2D electronic, magnetic and optoelectronic materials: (1) 2D semiconductor with high carrier mobility including monolayer δ -Cu₂S [1], GeAsSe, and SnSbTe [2]; (2) Janus group-III chalcogenide monolayers with enhanced piezoelectricity [3]; (3) monolayer group-III monochalcogenides by oxygen functionalization as 2D topological insulators [4]; (2) Y₂N monolayer as high-speed Dirac half-metal [5]; (5) monolayer MnB as 2D ferromagnet with high Curie temperature [6] (see Figure 1).

References

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- [2] Y. Guo, et al., *Frontier of Physics* 13 (2018) 138117
- [3] Y. Guo, et al., *Appl. Phys. Lett.* 110 (2017) 163102.
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- [5] Z. F. Liu, et al., *Nano Res.* 10 (2017) 1972.
- [6] Z. Jiang, et al., *Nanoscale Horizons* 3 (2018) 335.

Figures

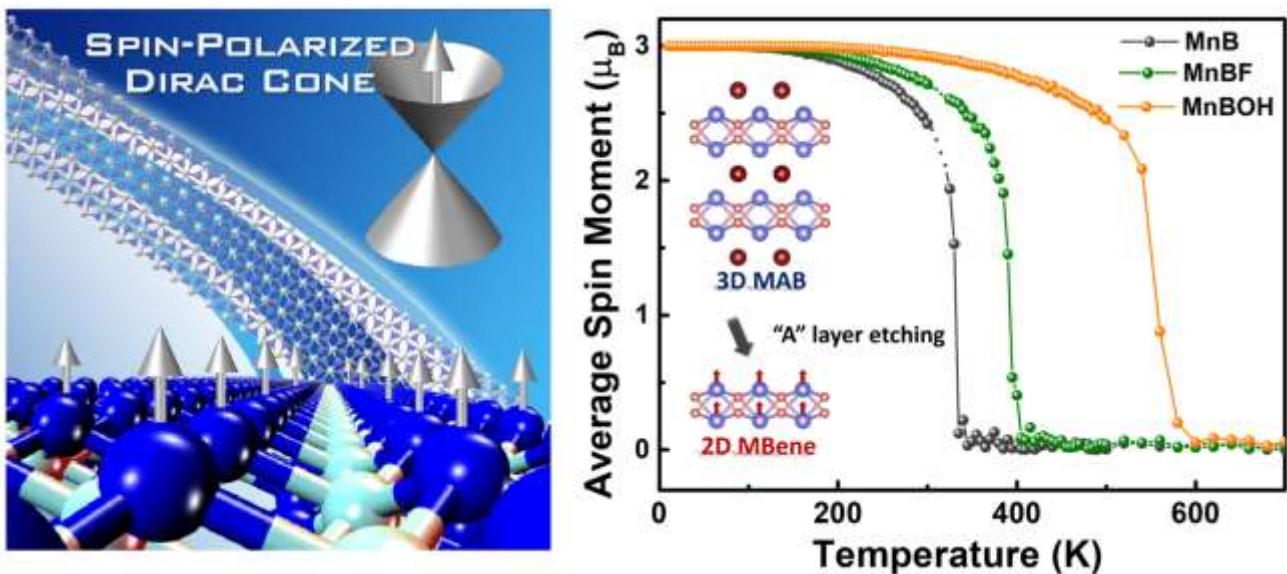


Figure 1: (left) Y₂N monolayer as a Dirac half-metal, (right) monolayer MnB as 2D ferromagnet with high Curie temperature.